Ordering number : ENN6921

NPN Triple Diffused Planar Silicon Transistor

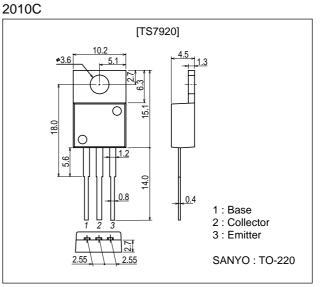


Features

- Best suited for push-pull inverter circuit.
- High breakdown voltage (VCBO=1200V).
- High reliability (Adoption of HVP process).
- · Adoption of MBIT process.

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		1200	V
Collector-to-Emitter Voltage	VCEO		600	V
Emitter-to-Base Voltage	VEBO		9	V
Collector Current	IC		4	Α
Collector Current (Pulse)	ICP		8	A
Collector Dissipation	PC		1.75	W
		Tc=25°C	70	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =600V, I _E =0			10	μA
Collector Cutoff Current	ICES	VCE=1200V, RBE=0			1.0	mA
Collector Sustain Voltage	VCEO(sus)	IC=100mA, IB=0	600			V
Emitter Cutoff Current	IEBO	V _{EB} =9V, I _C =0			1.0	mA

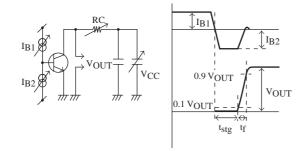
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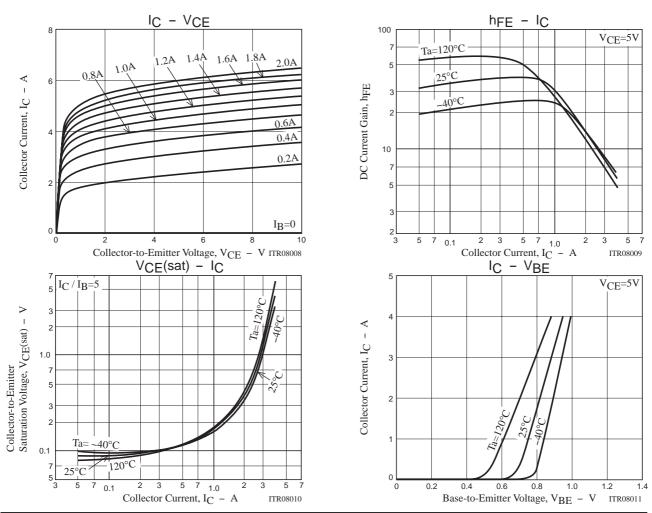
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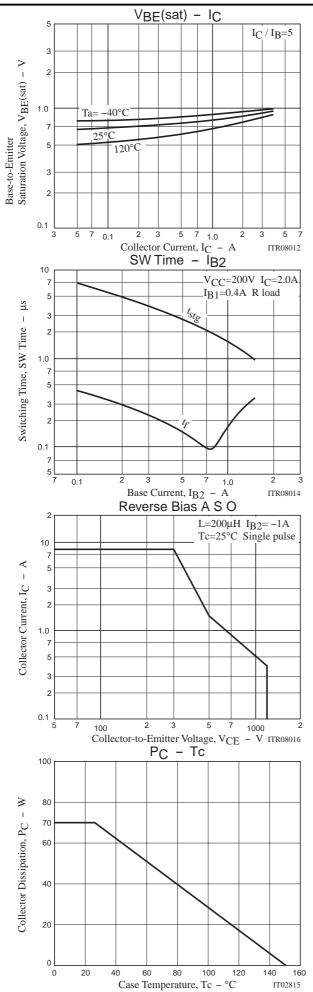
SANYO Electric Co., Ltd. Semiconductor Company TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN Continued from preceding page.

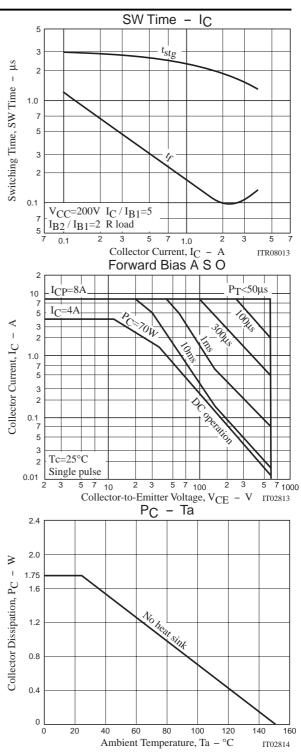
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
DC Current Gain	hFE1	V _{CE} =5V, I _C =0.3A	30	40	50	
	hFE2	V _{CE} =5V, I _C =1.5A	10			
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=2.0A, IB=0.4A			1.0	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =2.0A, I _B =0.4A			1.5	V
Storage Time	tstg	I _C =2.0A, I _{B1} =0.4A, I _{B2} =-0.8A			2.5	μs
Fall Time	tf	IC=2.0A, IB1=0.4A, IB2=-0.8A			0.15	μs

Switching Time Test Circuit









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